

FAST RECOVERY DIODE

APPLICATIONS

- Induction Heating.
- A.C. Motor Drives.
- Inverters And Choppers.
- Welding.
- High Frequency Rectification.
- UPS.

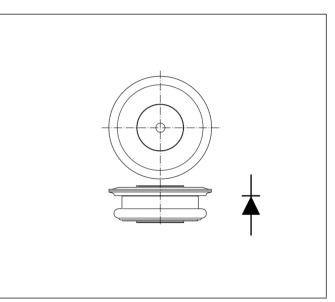
FEATURES

- Double Side Cooling.
- High Surge Capability.
- Low Recovery Charge.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V _{RRM} V	Conditions
DFS454 25	2500	$V_{RSM} = V_{RRM} + 100V$
DFS454 24	2400	
DFS454 22	2200	
DFS454 20	2000	

KEY PARAMETERS V_{RRM} 2500V I_{F(AV)} 365A I_{FSM} 3500A Q_r 200µC t_{rr} 2.0µs



Outline type code: M771. Turn to page 8 for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units			
Double Side Cooled							
I _{F(AV)}	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	365	A			
I _{F(RMS)}	RMS value	$T_{case} = 65^{\circ}C$	575	A			
I _F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	525	A			
Single Side Cooled (Anode side)							
l _{F(AV)}	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	242	A			
I _{F(RMS)}	RMS value	$T_{case} = 65^{\circ}C$	380	A			
I _F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	335	A			

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{FSM}	Surge (non-repetitive) forward current	10 ms half since with $0%$ V T = $150%$	3.5	kA
l ² t	I ² t for fusing	10ms half sine; with 0% V_{RRM} , $T_j = 150^{\circ}C$	61 x 10 ³	A²s
I _{FSM}	Surge (non-repetitive) forward current	$10mc$ holf since with 50% $V_{\rm cont} = 150\%$	2.8	kA
l²t	I ² t for fusing	10ms half sine; with 50% V_{RRM} , $T_j = 150^{\circ}C$	39.2 x 10 ³	A ² s
I _{FSM}	Surge (non-repetitive) forward current	10mc half since with $100%$ V T = $150%$	-	kA
l²t	I ² t for fusing	10ms half sine; with 100% V_{RRM} , $T_j = 150^{\circ}C$	-	A²s

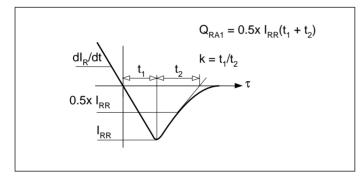
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	dc	-	0.07	°C/W
R _{th(j-c)}		Single side cooled	Anode dc	-	0.133	°C/W
			Cathode dc	-	0.147	°C/W
R _{th(c-h)}	Thermal resistance - case to heatsink	Clamping force 3.5kN with mounting compound	Double side	-	0.02	°C/W
			Single side	-	0.04	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	150	°C
T _{stg}	Storage temperature range			-55	175	°C
-	Clamping force			3.0	4.0	kN

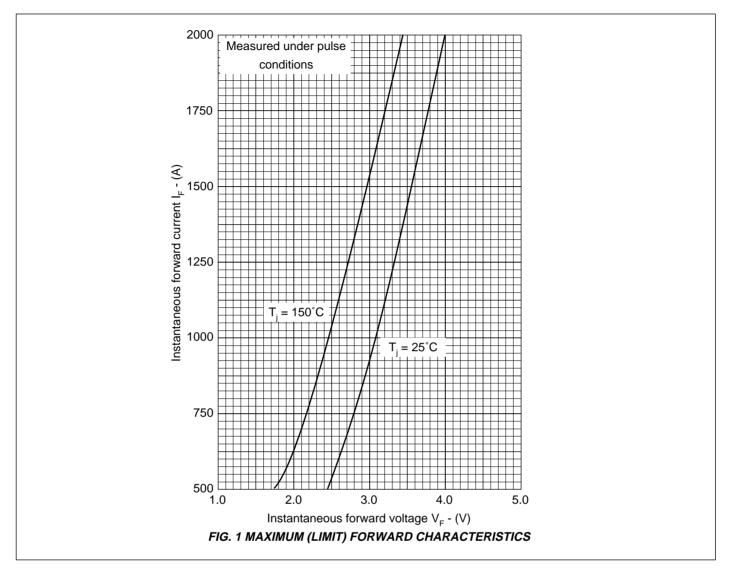
CHARACTERISTICS

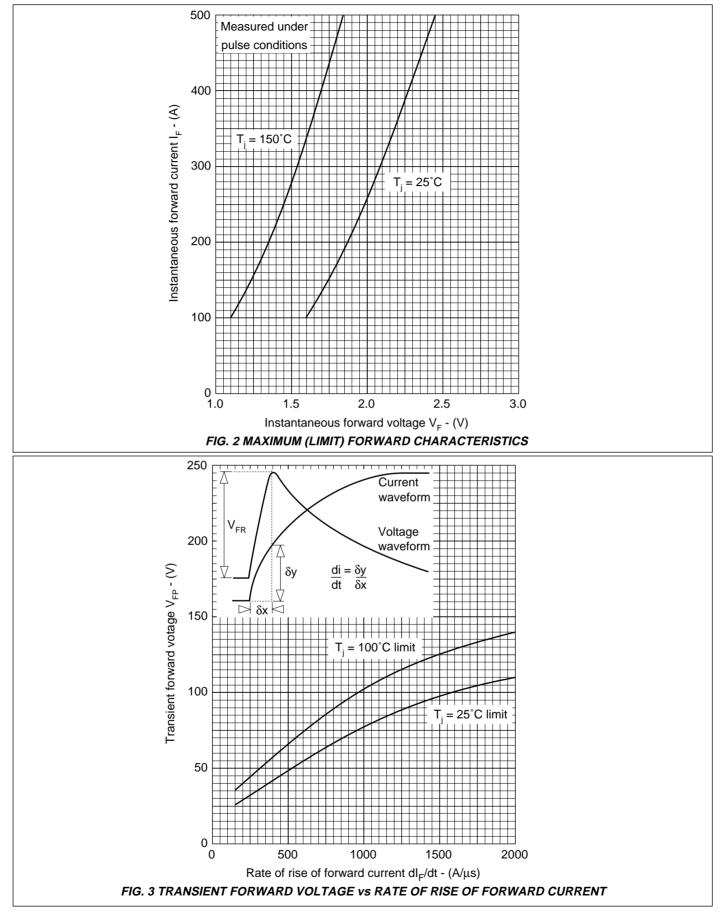
Symbol	Parameter	Conditions	Тур.	Max.	Units
V _{FM}	Forward voltage	At 1000A peak, T _{case} = 25°C	-	3.1	V
I _{RRM}	Peak reverse current	At V_{RRM} , $T_{\text{case}} = 150^{\circ}\text{C}$	-	50	mA
t _{rr}	Reverse recovery time		2.0	-	μs
Q _{RA1}	Recovered charge (50% chord)	I _F = 750A, di _{RR} /dt = 100A/μs	-	200	μC
I _{RM}	Reverse recovery current	T _{case} = 125°C, V _R = 100V	150	-	A
к	Soft factor		1.3	-	-
V _{TO}	Threshold voltage	At $T_{vj} = 150^{\circ}C$	-	1.64	V
r _T	Slope resistance	At $T_{vj} = 150^{\circ}C$	-	1.54	mΩ
V _{FRM}	Forward recovery voltage	di/dt = 1000A/µs, T _j = 125°C	-	120	V

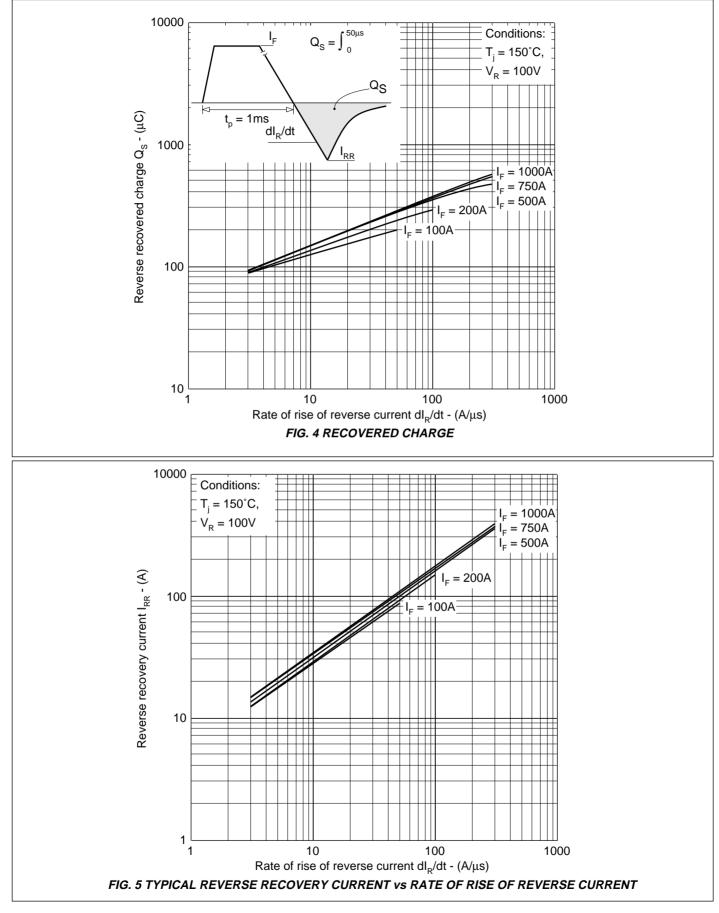
DEFINITION OF K FACTOR AND \mathbf{Q}_{RA1}

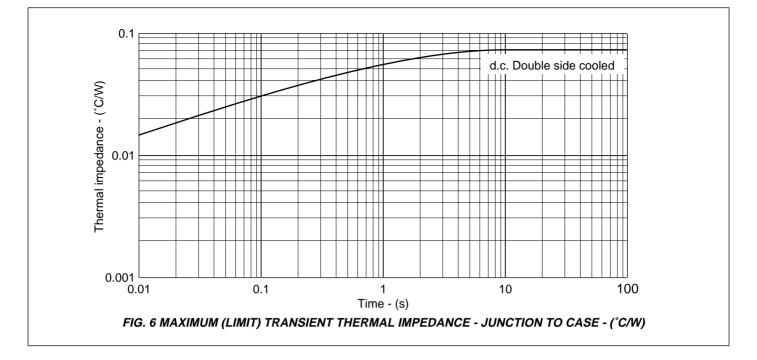


CURVES



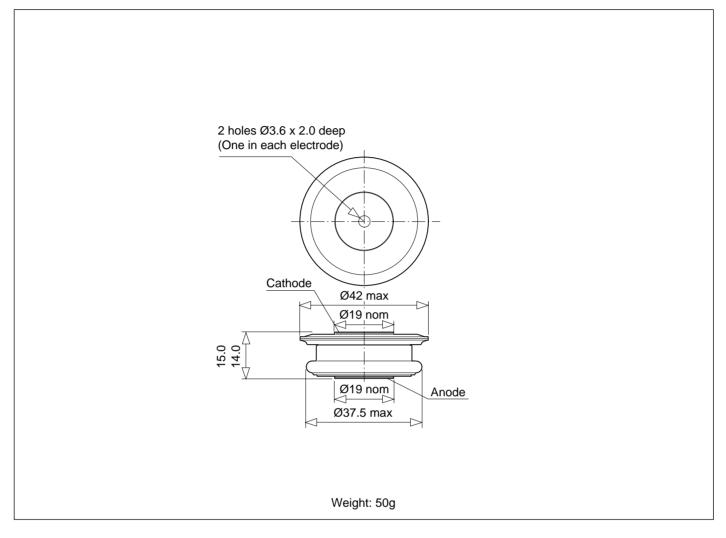






PACKAGE DETAILS - M771

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



GEC PLESSEY **SEMICONDUCTORS**

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